

# RJL5012DPP

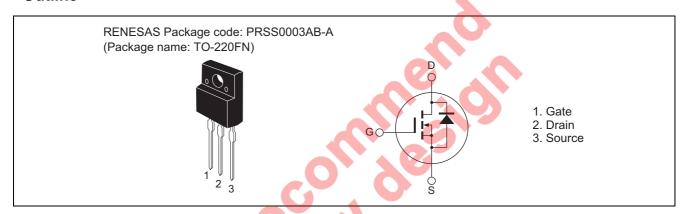
# Silicon N Channel MOS FET High Speed Power Switching

REJ03G1746-0200 Rev.2.00 Mar 05, 2009

### **Features**

- Built-in fast recovery diode
- Low on-resistance
- Low leakage current
- High speed switching

### **Outline**



# **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	500	V
Gate to source voltage	$V_{GSS}$	±30	V
Drain current	I <sub>D</sub> Note4	12	А
Drain peak current	I <sub>D (pulse)</sub> Note1	36	А
Body-drain diode reverse drain current	I <sub>DR</sub>	12	А
Body-drain diode reverse drain peak current	I <sub>DR (pulse)</sub> Note1	36	А
Avalanche current	I <sub>AP</sub> Note3	3	А
Avalanche energy	E <sub>AR</sub> Note3	0.5	mJ
Channel dissipation	Pch Note2	30	W
Channel to case thermal impedance	θch-c	4.17	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

- 2. Value at Tc = 25°C
- 3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C
- 4. Limited by maximum safe operation area

# **Electrical Characteristics**

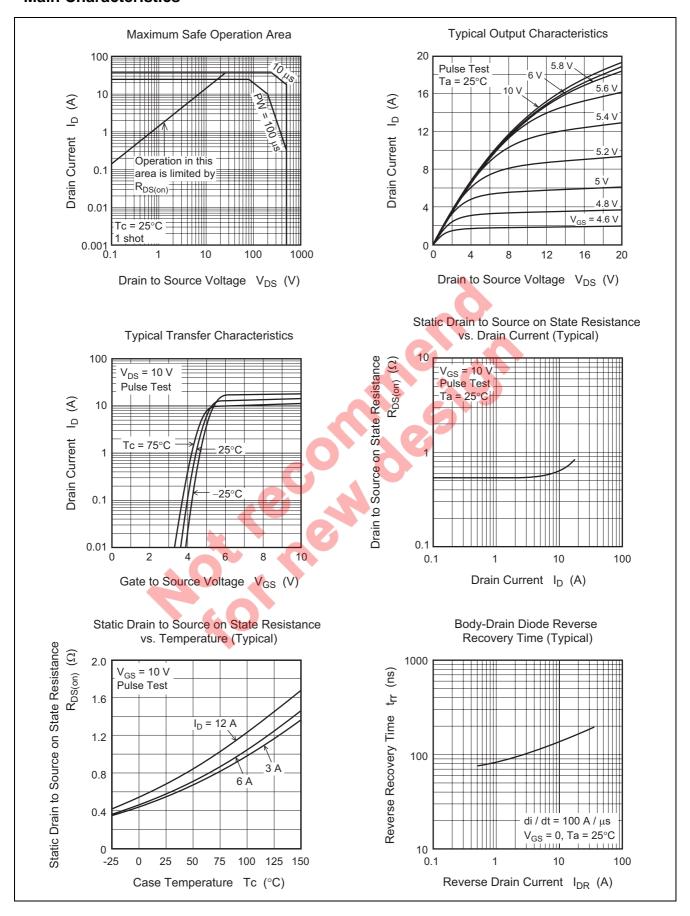
 $(Ta = 25^{\circ}C)$ 

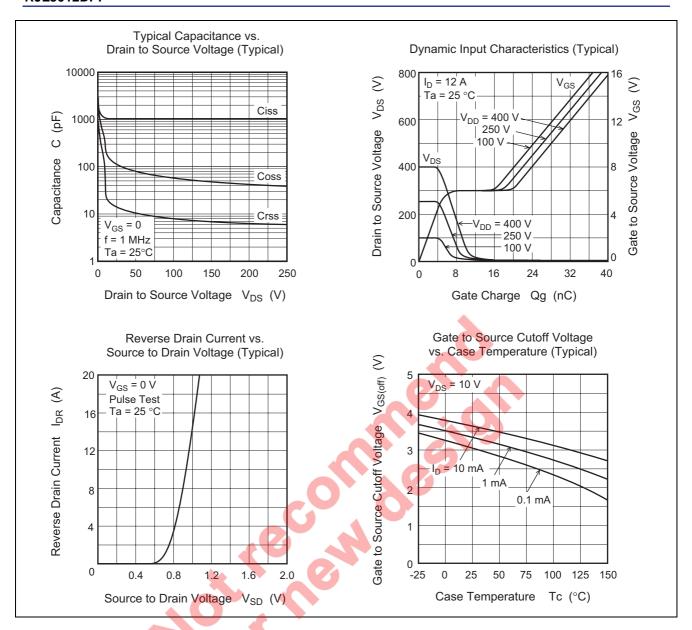
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	500	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	10	μΑ	$V_{DS} = 500 \text{ V}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	_	4.0	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R <sub>DS(on)</sub>		0.56	0.70	Ω	$I_D = 6 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note5}}$
Input capacitance	Ciss	_	1050	_	pF	V <sub>DS</sub> = 25 V
Output capacitance	Coss	_	115	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	14	_	pF	f = 1 MHz
Turn-on delay time	t <sub>d(on)</sub>	_	27	_	ns	I <sub>D</sub> = 6 A
Rise time	t <sub>r</sub>		22	_	ns	V <sub>GS</sub> = 10 V
Turn-off delay time	t <sub>d(off)</sub>		78	_	ns	$R_L = 41.7 \Omega$
Fall time	t <sub>f</sub>		15	_	ns	$Rg = 10 \Omega$
Total gate charge	Qg		27.8	_	nC	V <sub>DD</sub> = 400 V
Gate to source charge	Qgs		4.9		nC	V <sub>GS</sub> = 10 V
Gate to drain charge	Qgd	_	14.4	4	nC	I <sub>D</sub> = 12 A
Body-drain diode forward voltage	$V_{DF}$		0.96	1.60	V	I <sub>F</sub> = 12 A, V <sub>GS</sub> = 0 Note5
Body-drain diode reverse recovery time	t <sub>rr</sub>		140		ns	$I_F = 12 \text{ A}, V_{GS} = 0$
				•		di <sub>F</sub> /dt = 100 A/μs
Collings						
	40	-				
Body-drain diode reverse recovery time t <sub>rr</sub> — 140 — ns t <sub>F</sub> = 12 A, V <sub>GS</sub> = 0 di <sub>F</sub> /dt = 100 A/μs  Notes: 5. Pulse test						

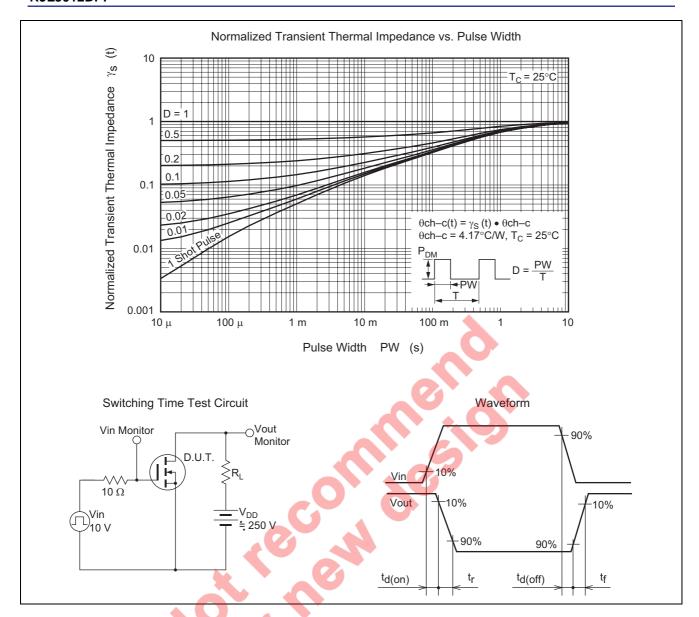
Notes: 5. Pulse test



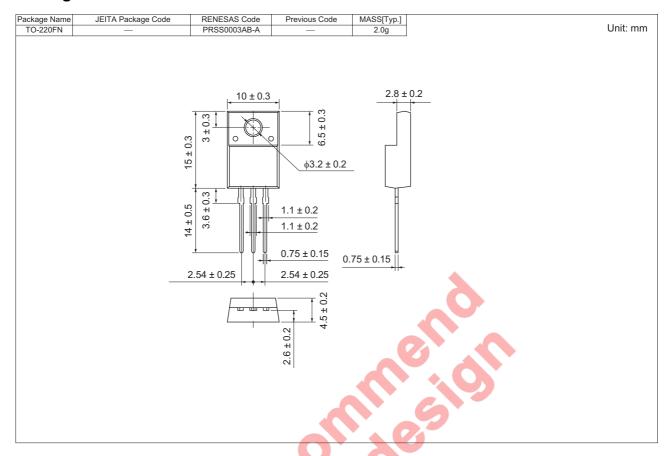
### **Main Characteristics**







# **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	1	Shipping Container
RJL5012DPP-00-T2	1050 pcs		ox (Tube)

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